PATENT ASSIGNMENT

Electronic Version v1.1
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SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
Formosa Epitaxy Incorporation	04/21/2009

RECEIVING PARTY DATA

Name:	Lumens Co., Ltd.
Street Address:	456 Gomae-Dong, Giheung-Gu
Internal Address:	Yongin-si
City:	Gyeonggi-do
State/Country:	REPUBLIC OF KOREA
Postal Code:	449-901

Name:	Formosa Epitaxy Incorporation
Street Address:	No. 99, Lung-Yuan 1st Road
Internal Address:	Lung-Tan Ind. Park
City:	Lung-Tan, Tao-Yung Hsien
State/Country:	TAIWAN

PROPERTY NUMBERS Total: 21

Property Type	Number
Patent Number:	7173289
Patent Number:	6753552
Patent Number:	7442962
Patent Number:	7374958
Patent Number:	7345321
Patent Number:	7307291
Patent Number:	7180097
Patent Number:	7180096
Patent Number:	7148519

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Patent Number:	7042018
Patent Number:	7033949
Patent Number:	6967346
Patent Number:	6979835
Patent Number:	6841804
Patent Number:	6914264
Patent Number:	6248608
Patent Number:	7105850
Patent Number:	7087924
Patent Number:	7087922
Patent Number:	7049638
Patent Number:	7042019

CORRESPONDENCE DATA

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ATTORNEY DOCKET NUMBER:	090211FO
NAME OF SUBMITTER:	Jason Z. Lin

Total Attachments: 2
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DEED OF ASSIGNMENT

WHEREAS, I/we, **Formosa Epitaxy Incorporation**, whose post office address(es) appear(s) below, hereinafter referred to as ASSIGNOR, is the sole owner of the following patents issued by the United States Patent and Trade mark Office (hereinafter "PATENTs"):

	Title	Patent No.
1.	Light Emitting Diode Structure Having Photonic Crystals	7,173,289
2.	Growth-Selective Structure Of Light-Emitting Diode	6,753,552
3.	High-Brightness Gallium-Nitride Based Light Emitting Diode Structure	7,442,962
4.	Light Emitting Semiconductor Bonding Structure And Method Of Manufacturing The Same	7,374,958
5.	High-Brightness Gallium-Nitride Based Light Emitting Diode Structure	7,345,321
6.	Gallium-Nitride Based Ultraviolet Photo Detector	7,307,291
7.	High-Brightness Gallium-Nitride Based Light Emitting Diode Structure	7,180,097
8.	Gallium-Nitride Based Light-Emitting Diode Structure With High Reverse Withstanding Voltage And Anti-ESD Capability	7,180,096
9.	Structure Of GaN Light-Emitting Diode	7,148,519
10.	Structure Of GaN Light-Emitting Diode	7,042,018
11.	Structure And Manufacturing Method For Nitride-Based Light-Emitting Diodes	7,033,949
12.	Light Emitting Diode Structure And Manufacture Method Thereof	6,967,346
13.	Gallium-Nitride Based Light-Emitting Diode Epitaxial Structure	6,979,835
14.	Device Of White Light-Emitting Diode	6,841,804
15.	Structure And Manufacturing Method For GaN Light Emitting Diodes	6,914,264
16.	Manufacturing Method Of A Gallium Nitride-Based Blue Light Emitting Diode (LED) OHMIC Electrodes	6,248,608
17.	GaN LED Structure With P-Type Contacting Layer Grown At Low-Temperature And Having Low Resistivity	7,105,850
18.	Gallium-Nitride Based Light Emitting Diode Structure With Enhanced Light Illuminance	7,087,924
19.	Light-Emitting Diode Structure	7,087,922
20.	High-Brightness Gallium-Nitride Based Light Emitting Diode Structure	7,049,638
21.	Gallium-Nitride Based Multi-Quantum Well Light-Emitting Diode N-Type Contact Layer Structure	7,042,019

WHEREAS, **LUMENS CO., LTD.** having its office located at **456 Gomae-Dong, Giheung-Gu, Yongin-si, Gyeonggi-do, Korea 449-901** and **Formosa Epitaxy Incorporation** having its office located at **No.99, Lung-Yuan 1st Road, Lung-Tan Ind. Park, Lung-Tan, Tao-Yung Hsien, Taiwan, R.O.C.** hereinafter referred to as assignees, are desirous of acquiring the entire right, title and interest in and to the same in the United States;

NOW, THEREFORE, for good and valuable consideration, the ASSIGNOR hereby sells, assigns and transfers to the assignees the entire right, title and interest in and to the PATENTs and its successors, **in accordance with the following percentiles of ownership interest: Five percent (5%) to LUMENS CO., LTD., Ninety-Five percent (95%) to Formosa Epitaxy Incorporation.**

ASSIGNOR hereby covenants that no assignment, sale, agreement or encumbrance has been or will be made or entered into which would conflict with this assignment and sale.

ASSIGNOR further covenants that ASSIGNEEs will, upon his request, be provided promptly with all pertinent facts and documents to said PATENTs as may be known and accessible to ASSIGNOR and will testify as to the same in any interference, litigation or proceeding related hereto and will promptly execute and delivery to ASSIGNEEs or his legal representatives any and all papers, instruments or affidavits required to obtain, maintain, issue and enforce said PATENTs which may be necessary or desirable to carry our the purpose thereof.

Assignor Name Fen-Ren Chien	Address **No.99, Lung-Yuan 1st Road, Lung-Tan Ind. Park, Lung-Tan, Tao-Yung Hsien, Taiwan, R.O.C.**
Signature	
Title President	
Where Signed **Taiwan, R. O. C.**	Date April 21, 2009

Assignee Name Tae-Kyung Yoo	Address **456 Gomae-Dong, Giheung-Gu, Yongin-si, Gyeonggi-do, Korea 449-901**
Signature Tae-Kyung Yoo.	
Title President	
Where Signed Taiwan	Date April 21, 2009

Assignee Name Fen-Ren Chien	Address **No.99, Lung-Yuan 1st Road, Lung-Tan Ind. Park, Lung-Tan, Tao-Yung Hsien, Taiwan, R.O.C.**
Signature	
Title President	
Where Signed **Taiwan, R. O. C.**	Date April 21, 2009